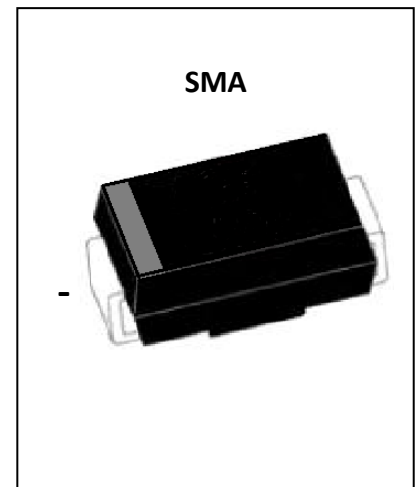


SR3100L Schottky Barrier Diode
Feature

- Low VF
- High Junction Temperature
- High surge current capability

Applications

- Rectifier

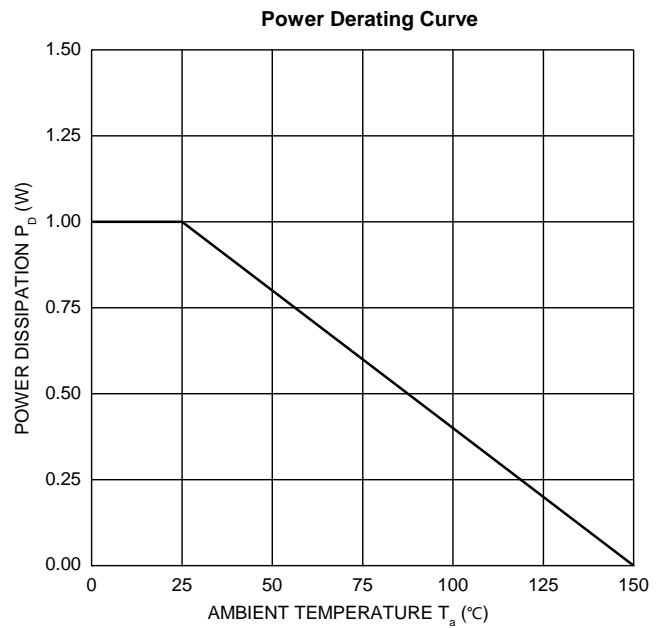
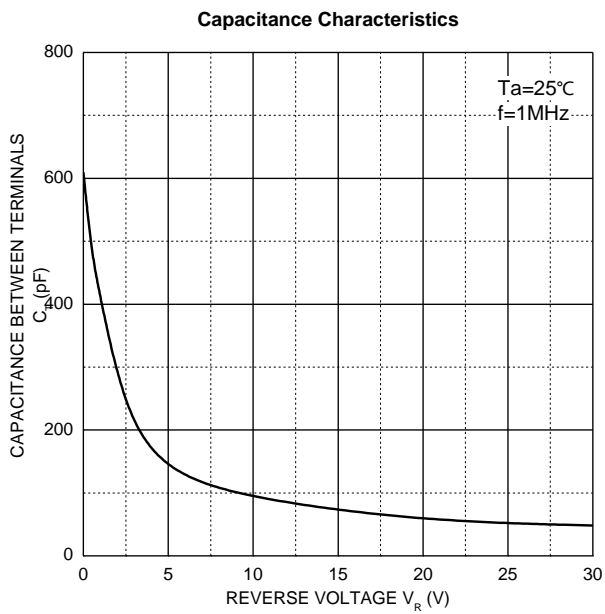
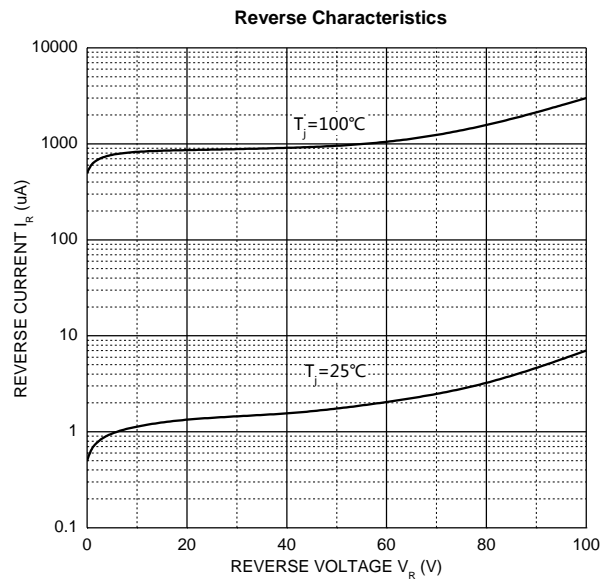
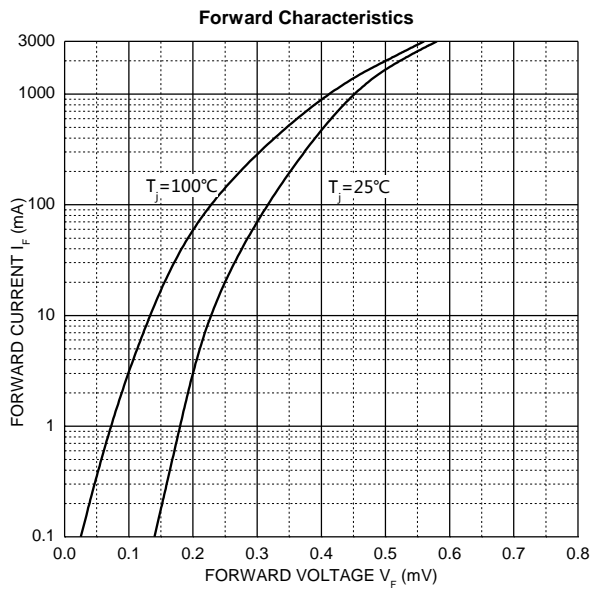

ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
DC reverse voltage	V _R	100	V
Mean rectifying current	I _O	3.0	A
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I _{FSM}	120	A
Power Dissipation	P _D	1.0	W
Thermal Resistance from Junction to Ambient	R _{θJA}	120	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

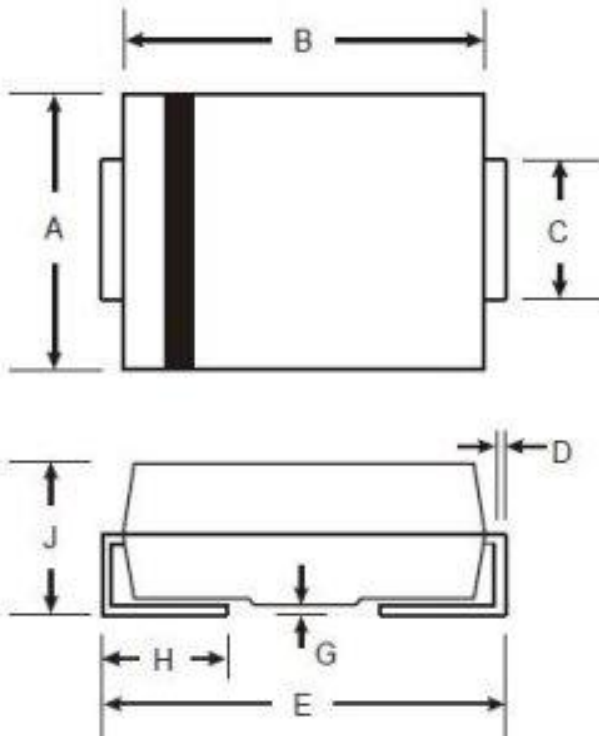
ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	V _{BR}	I _R =250μA	100	110		V
Forward voltage	V _F	I _F =1A	0	0.45	0.50	V
		I _F =3A	0	0.58	0.64	V
Reverse current	I _R	V _R =100V		10	50	μA
		V _R =100V, T _a =100°C			20	mA
Diode capacitance	C _D	VR=4V, f=1MHz		170		pF

Typical Characteristics



SMA Package Outline Dimensions



SMA		
Dim	Min	Max
A	2.29	2.92
B	4.00	4.60
C	1.27	1.63
D	0.15	0.31
E	4.80	5.59
G	0.05	0.20
H	0.76	1.52
J	2.01	2.30

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)